

Cent Subg d¹²nt

a source region having the first conductive type and provided on the channel region, the source region is located substantially at a center of the channel region, and the source region is isolated from the insulation film, wherein an impurity concentration of the channel region is equal to or less than an impurity concentration in the drift region, and a depletion layer forms over the entire channel region sandwiched between the gate region when a zero bias is applied to the gate region.

G² Sub¹ fig 8 112 1st

26. (Twice Amended) The semiconductor device according to claim 1, further comprising a semiconductor layer having the second conductive type located between the source region and the source electrode, the semiconductor layer including an end face extended to a position covering at least a portion of the gate region.

G³ Sub¹ fig 8 112 1st

30. (Three Times Amended) A semiconductor device comprising:

fig. 14B

a first cathode region having a first conductive type;

a second cathode region having the first conductive type and disposed on the first cathode region;

a first anode region having a second conductive type and provided on the

second cathode region;

a trench structure provided so as to surround at least the first anode region via an insulation film; and

a second anode region having the second conductive type and provided on the

first anode region, wherein an impurity concentration in the first anode region is equal to or

less than an impurity concentration in the second cathode. region]

REMARKS

Claims 1, 4, 12 and 20-30 are pending. By this Amendment, claims 12, 26 and 30 are amended. Reconsideration based on the following remarks is respectfully requested.